

## SSH10N80A-VB Datasheet

## N-Channel 800V (D-S) Super Junction Power MOSFET

## PRODUCT SUMMARY

|                                         |                 |      |
|-----------------------------------------|-----------------|------|
| $V_{DS}$ (V) at $T_J$ max.              | 850             |      |
| $R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C | $V_{GS} = 10$ V | 0.40 |
| $Q_g$ max. (nC)                         | 88              |      |
| $Q_{gs}$ (nC)                           | 9               |      |
| $Q_{gd}$ (nC)                           | 16              |      |
| Configuration                           | Single          |      |

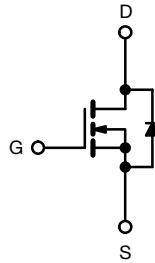
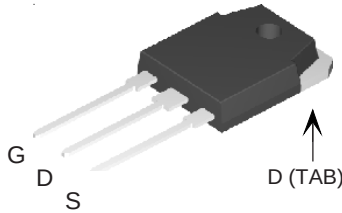
## FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)



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## TO-3P



N-Channel MOSFET

## APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$  °C, unless otherwise noted)

| PARAMETER                                                 | SYMBOL           | LIMIT          | UNIT |
|-----------------------------------------------------------|------------------|----------------|------|
| Drain-source voltage                                      | $V_{DS}$         | 800            | V    |
| Gate-source voltage                                       | $V_{GS}$         | $\pm 30$       |      |
| Continuous drain current ( $T_J = 150$ °C)                | $V_{GS}$ at 10 V | $T_C = 25$ °C  | 11   |
|                                                           |                  | $T_C = 100$ °C | 8    |
| Pulsed drain current <sup>a</sup>                         | $I_{DM}$         | 32             | A    |
| Linear derating factor                                    |                  | 1.4            | W/°C |
| Single pulse avalanche energy <sup>b</sup>                | $E_{AS}$         | 226            | mJ   |
| Maximum power dissipation                                 | $P_D$            | 179            | W    |
| Operating junction and storage temperature range          | $T_J, T_{stg}$   | -55 to +150    | °C   |
| Drain-source voltage slope                                | $dV/dt$          | $T_J = 125$ °C | 70   |
| Reverse diode $dV/dt$ <sup>d</sup>                        |                  |                | 4.3  |
| Soldering recommendations (peak temperature) <sup>c</sup> | For 10 s         | 300            | °C   |

## Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 4.0$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C

**THERMAL RESISTANCE RATINGS**

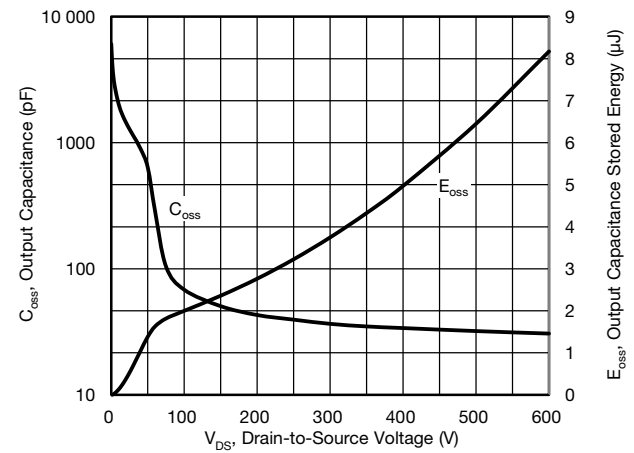
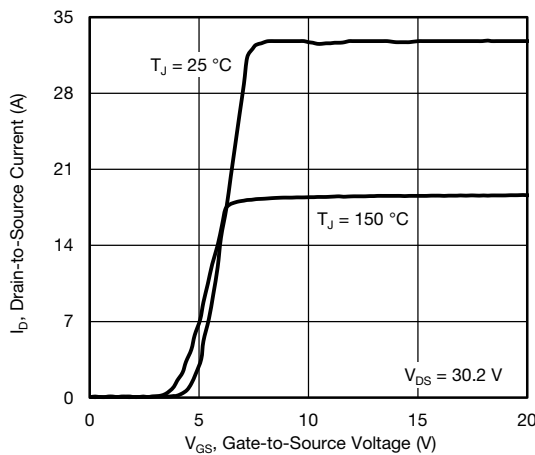
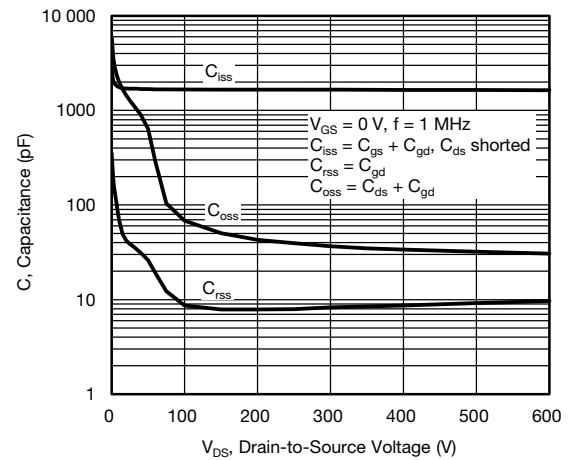
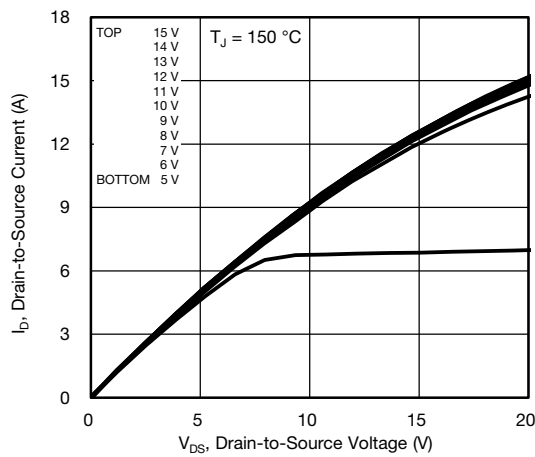
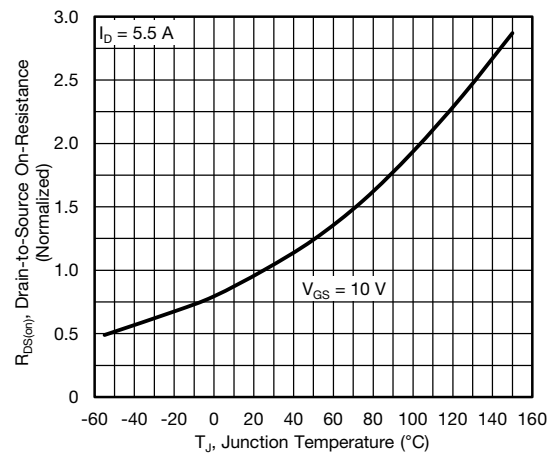
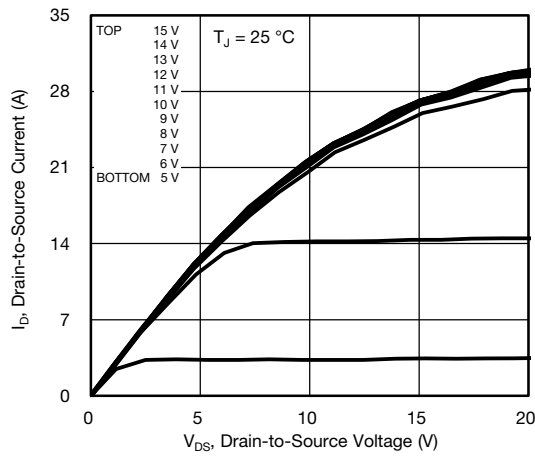
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum junction-to-ambient      | $R_{thJA}$ | -    | 62   | °C/W |
| Maximum junction-to-case (drain) | $R_{thJC}$ | -    | 0.7  |      |

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER                                                 | SYMBOL              | TEST CONDITIONS                                                                                                                                          |                                                | MIN. | TYP. | MAX.      | UNIT               |
|-----------------------------------------------------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------|------|------|-----------|--------------------|
| Static                                                    |                     |                                                                                                                                                          |                                                |      |      |           |                    |
| Drain-source breakdown voltage                            | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                   |                                                | 800  | -    | -         | V                  |
| $V_{DS}$ temperature coefficient                          | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$                                                                                            |                                                | -    | 1.1  | -         | $V/^\circ\text{C}$ |
| Gate-source threshold voltage (N)                         | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                       |                                                | 2    | -    | 4         | V                  |
| Gate-source leakage                                       | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$                                                                                                                               |                                                | -    | -    | $\pm 100$ | nA                 |
|                                                           |                     | $V_{GS} = \pm 30\text{ V}$                                                                                                                               |                                                | -    | -    | $\pm 1$   | $\mu\text{A}$      |
| Zero gate voltage drain current                           | $I_{DSS}$           | $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                                          |                                                | -    | -    | 1         | $\mu\text{A}$      |
|                                                           |                     | $V_{DS} = 640\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$                                                                      |                                                | -    | -    | 10        |                    |
| Drain-source on-state resistance                          | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$                                                                                                                                   | $I_D = 5.5\text{ A}$                           | -    | 0.40 | -         | $\Omega$           |
| Forward transconductance                                  | $g_{fs}$            | $V_{DS} = 30\text{ V}$ , $I_D = 5.5\text{ A}$                                                                                                            |                                                | -    | 4.5  | -         | S                  |
| Dynamic                                                   |                     |                                                                                                                                                          |                                                |      |      |           |                    |
| Input capacitance                                         | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 100\text{ V}$ ,<br>$f = 1\text{ MHz}$                                                                               |                                                | -    | 1670 | -         | pF                 |
| Output capacitance                                        | $C_{oss}$           |                                                                                                                                                          |                                                | -    | 68   | -         |                    |
| Reverse transfer capacitance                              | $C_{rss}$           |                                                                                                                                                          |                                                | -    | 9    | -         |                    |
| Effective output capacitance, energy related <sup>a</sup> | $C_{o(er)}$         | $V_{DS} = 0\text{ V to } 480\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                           |                                                | -    | 43   | -         |                    |
| Effective output capacitance, time related <sup>b</sup>   | $C_{o(tr)}$         |                                                                                                                                                          |                                                | -    | 212  | -         |                    |
| Total gate charge                                         | $Q_g$               | $V_{GS} = 10\text{ V}$                                                                                                                                   | $I_D = 5.5\text{ A}$ , $V_{DS} = 480\text{ V}$ | -    | 44   | 88        | nC                 |
| Gate-source charge                                        | $Q_{gs}$            |                                                                                                                                                          |                                                | -    | 9    | -         |                    |
| Gate-drain charge                                         | $Q_{gd}$            |                                                                                                                                                          |                                                | -    | 16   | -         |                    |
| Turn-on delay time                                        | $t_{d(on)}$         | $V_{DD} = 480\text{ V}$ , $I_D = 5.5\text{ A}$ ,<br>$V_{GS} = 10\text{ V}$ , $R_g = 9.1\text{ }\Omega$                                                   |                                                | -    | 18   | 36        | ns                 |
| Rise time                                                 | $t_r$               |                                                                                                                                                          |                                                | -    | 15   | 30        |                    |
| Turn-off delay time                                       | $t_{d(off)}$        |                                                                                                                                                          |                                                | -    | 55   | 110       |                    |
| Fall time                                                 | $t_f$               |                                                                                                                                                          |                                                | -    | 18   | 36        |                    |
| Gate input resistance                                     | $R_g$               | $f = 1\text{ MHz}$ , open drain                                                                                                                          |                                                | 0.4  | 0.9  | 1.8       | $\Omega$           |
| Drain-Source Body Diode Characteristics                   |                     |                                                                                                                                                          |                                                |      |      |           |                    |
| Continuous source-drain diode current                     | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode<br> |                                                | -    | -    | 12        | A                  |
| Pulsed diode forward current                              | $I_{SM}$            |                                                                                                                                                          |                                                | -    | -    | 32        |                    |
| Diode forward voltage                                     | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_S = 5.5\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                          |                                                | -    | -    | 1.2       | V                  |
| Reverse recovery time                                     | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_F = I_S = 5.5\text{ A}$ ,<br>$di/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 25\text{ V}$                              |                                                | -    | 345  | 690       | ns                 |
| Reverse recovery charge                                   | $Q_{rr}$            |                                                                                                                                                          |                                                | -    | 4.2  | 8.4       | $\mu\text{C}$      |
| Reverse recovery current                                  | $I_{RRM}$           |                                                                                                                                                          |                                                | -    | 21   | -         | A                  |

**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$   
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


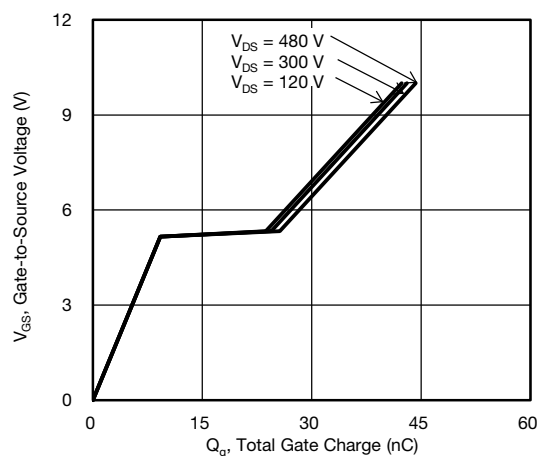


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

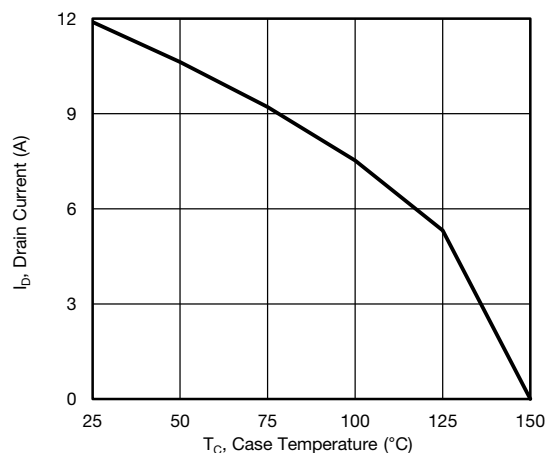


Fig. 10 - Maximum Drain Current vs. Case Temperature

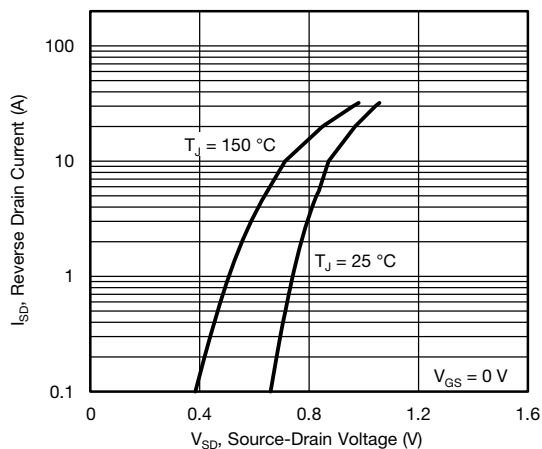


Fig. 8 - Typical Source-Drain Diode Forward Voltage

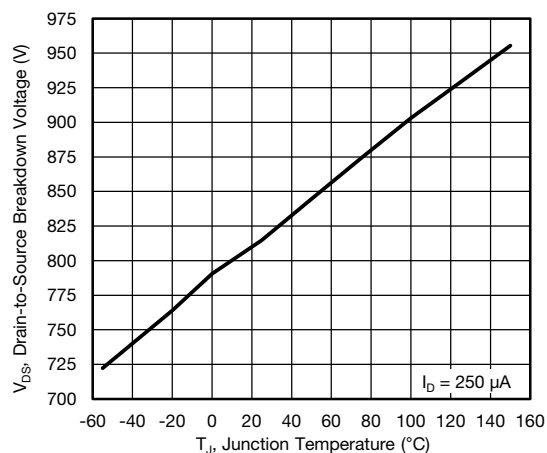


Fig. 11 - Temperature vs. Drain-to-Source Voltage

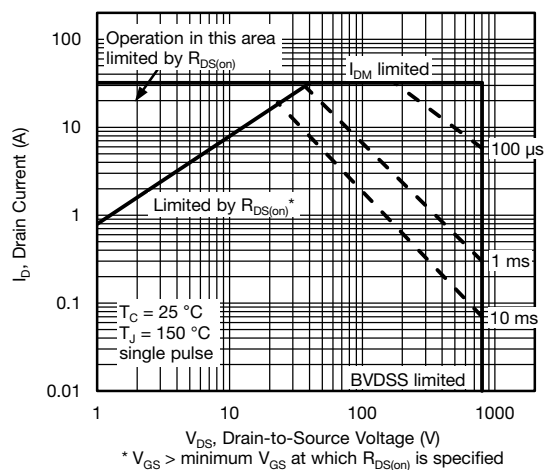


Fig. 9 - Maximum Safe Operating Area

\*  $V_{GS} > \text{minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$

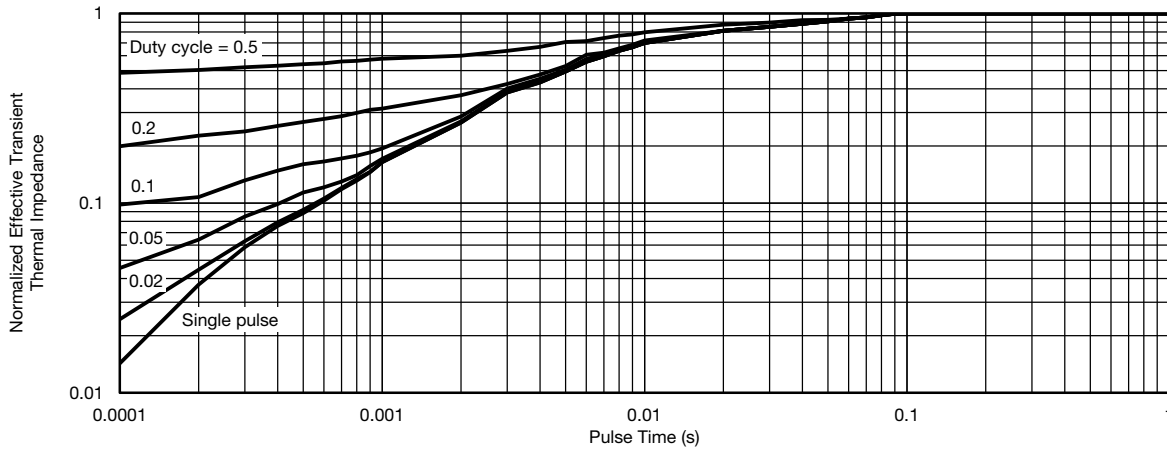


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

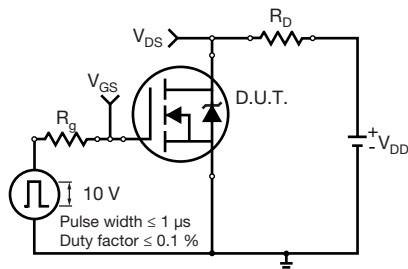


Fig. 13 - Switching Time Test Circuit

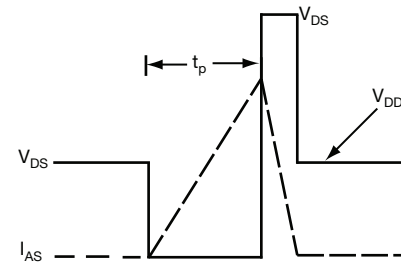


Fig. 16 - Unclamped Inductive Waveforms

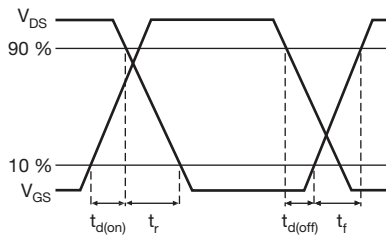


Fig. 14 - Switching Time Waveforms

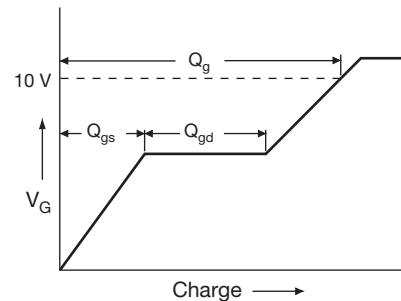


Fig. 17 - Basic Gate Charge Waveform

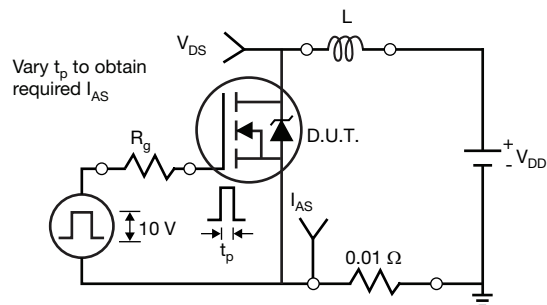


Fig. 15 - Unclamped Inductive Test Circuit

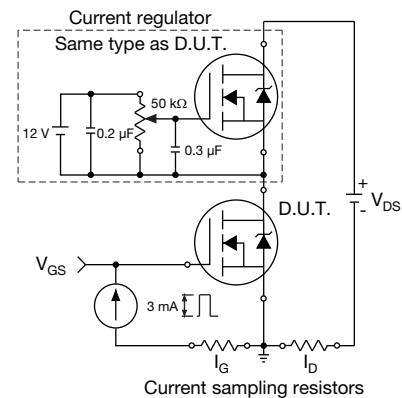
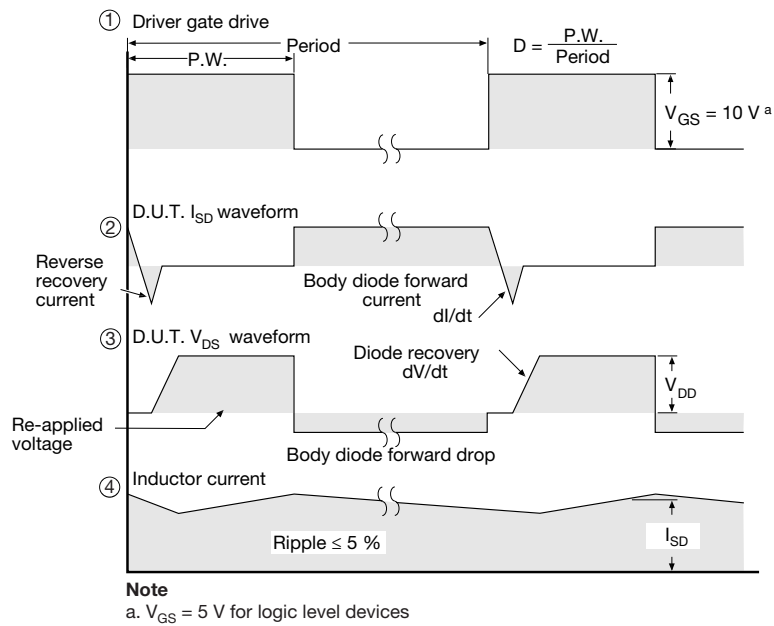
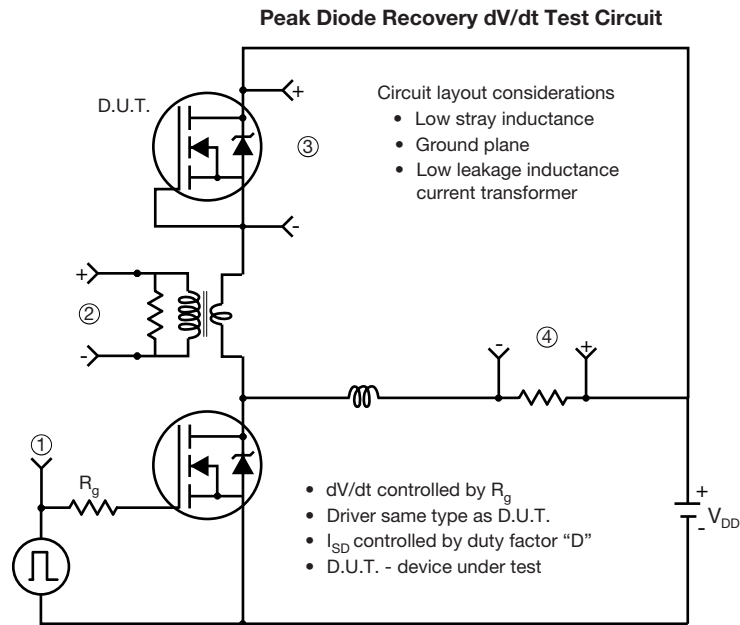
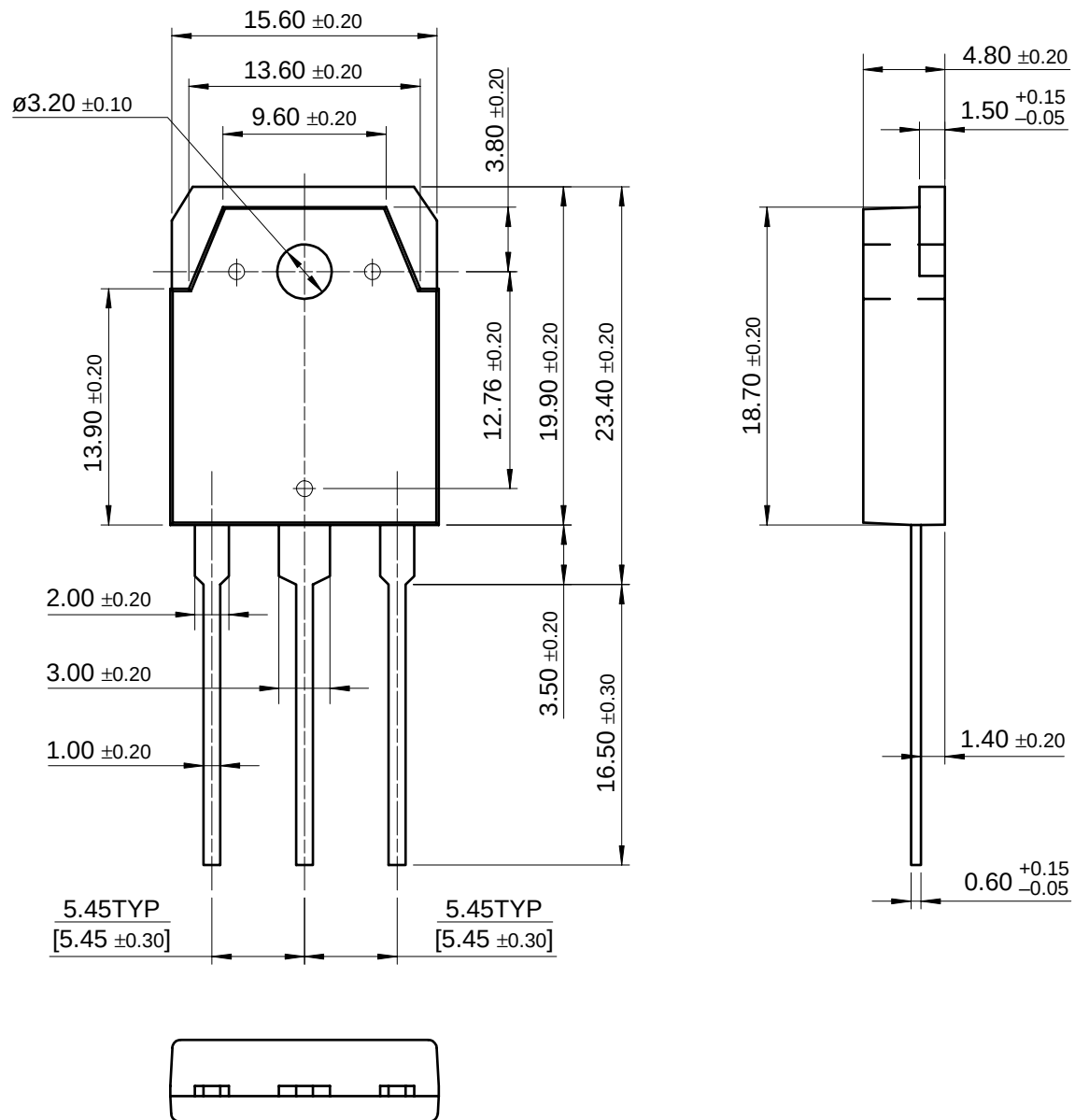


Fig. 18 - Gate Charge Test Circuit



**Fig. 19 - For N-Channel**

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